



POCKET NO. CHEN 4-17-157

PATENT ^B

#25-000

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Yuanning Chen, et al.

Serial No.: 09/597,076

Filed: June 20, 2000

For: TWO-STEP OXIDATION PROCESS FOR OXIDIZING A SILICON SUBSTRATE WHEREIN THE FIRST STEP IS CARRIED OUT AT A TEMPERATURE BELOW THE VISCOELASTIC TEMPERATURE OF SILICON DIOXIDE AND THE SECOND STEP IS CARRIED OUT AT A TEMPERATURE ABOVE THE VISCOELASTIC TEMPERATURE

Group: 2813

Examiner: Kielin, Erik J.

Date Mailed: November 15, 2002

Commissioner for Patents
Washington, D. C. 20231

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on

2-4-2003 Date

Erik J. Kielin Signature

(Printed or typed name of person signing the certificate)

(Signature of the person signing the certificate)

Sir:

LETTER TO OFFICIAL DRAFTSMAN

Transmitted herewith are Nine sheets of formal drawings to be substituted for the informal drawings initially filed in the above-identified application for patent.

Respectfully submitted,

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